

1 1. A method comprising:
2 monitoring the temperature of a cache memory; and
3 in response to a detection of a temperature
4 condition, transitioning the cache memory from a write-back
5 cache to a write-through cache.

1 2. The method of claim 1 including monitoring the
2 temperature of a ferroelectric polymer cache memory.

1 3. The method of claim 1 including adjusting the
2 operation of a system using said memory at a first
3 temperature and, in response to the detection of a higher,
4 second temperature, transitioning the cache from a write-
5 back cache to a write-through cache.

1 4. The method of claim 3, including slowing an
2 operation of said system at said first temperature.

1 5. The method of claim 3 including reducing pre-
2 fetching at said first temperature.

1 6. The method of claim 3 including adjusting what
2 data is cached based on the detection of said first
3 temperature.

1 7. The method of claim 3 including shutting off the
2 said cache memory at a temperature above said second
3 temperature.

1 8. The method of claim 7 including monitoring for a
2 temperature lower than said second temperature.

1 9. The method of claim 8 including, upon detecting a
2 lower temperature, resuming operation of said cache memory.

1 10. The method of claim 8 including waiting for a
2 power cycle before resuming cache operations.

1 11. The method of claim 7 including shutting off said
2 cache memory and invalidating cache lines in said cache
3 memory.

1 12. The method of claim 1 including flushing a cache
2 line in said cache memory that has not been written through
3 to a source memory.

1 13. An article comprising a medium storing
2 instructions that, if executed, enable a processor-based
3 system to:

4 monitor the temperature of a cache memory; and

5 in response to the detection of a temperature
6 condition, transition the cache memory from a write-back
7 cache to a write-through cache memory.

1 14. The article of claim 13 further storing
2 instructions that, if executed, enable a processor-based
3 system to monitor the temperature of a ferroelectric
4 polymer cache memory.

1 15. The article of claim 13 further storing
2 instructions that, if executed, enable a processor-based
3 system to adjust the operation of a system using said
4 memory at a first temperature and, in response to the
5 detection of a higher, second temperature, transition the
6 cache memory from a write-back to a write-through cache.

1 16. The article of claim 13 further storing
2 instructions that, if executed, enable a processor-based
3 system to shut off the said cache memory at a temperature
4 above said second temperature.

1 17. The article of claim 13 further storing
2 instructions that, if executed, enable a processor-based
3 system to flush a cache line in said cache memory that has
4 not been written through to a source memory.

1 18. The article of claim 17 further storing
2 instructions that, if executed, enable a processor-based
3 system to monitor for a temperature lower than said second
4 temperature.

1 19. The article of claim 18 further storing
2 instructions that, if executed, enable a processor-based
3 system to resume operation of said cache memory upon
4 detecting a lower temperature.

1 20. The article of claim 18 further storing
2 instructions that, if executed, enable a processor-based
3 system to wait for a power cycle before resuming cache
4 operations.

1 21. The article of claim 16 further storing
2 instructions that, if executed, enable a processor-based
3 system to shut off the cache and invalidate all the cache
4 lines.

1 22. The article of claim 13 further storing
2 instructions that, if executed, enable a processor-based
3 system to transition the cache memory from a write-back to
4 cache to a write-through cache memory at a first, higher
5 temperature and to adjust for the slower speed of the cache

6 memory at a second temperature lower than said first
7 temperature.

1 23. The article of claim 22 further storing
2 instructions that, if executed, enable a processor-based
3 system to reduce the speed of operations at said second
4 temperature.

1 24. The article of claim 22 further storing
2 instructions that, if executed, enable a processor-based
3 system to reduce pre-fetching at said second temperature.

1 25. The article of claim 22 further storing
2 instructions that, if executed, enable a processor-based
3 system to adjust the caching of data based on the detection
4 of said second temperature.

1 26. A processor-based system comprising:
2 a processor;
3 a disk drive coupled to said processor;
4 a cache memory coupled said processor; and
5 a storage to store a cache driver to monitor the
6 temperature of said cache memory and in response to the
7 detection of a temperature condition, transition the cache
8 memory from a write-back cache memory to a write-through
9 cache memory.

1 27. The system of claim 26 wherein said cache memory
2 is a ferroelectric polymer cache memory.

1 28. The system of claim 26 wherein said cache memory
2 is a flash memory.

1 29. The system of claim 26 wherein said storage
2 stores instructions that enable dirty lines to be flushed.

1 30. The system of claim 26 wherein said storage
2 stores instructions that enable the system to adjust for
3 reduced speed operation at a first temperature, switch to a
4 write-through cache memory at a second higher temperature,
5 and invalidate cache lines and shut off the cache memory at
6 still a higher temperature.

1 31. The system of claim 30, said storage further
2 storing instructions that enable the cache memory to return
3 to full speed operation.

1 32. The system of claim 30 wherein said storage
2 stores instructions that enable the system to wait for
3 reduced speed temperature range to resume cache operations
4 after shutting off the cache memory in response to a
5 temperature condition.

1 33. The system of claim 30 wherein said storage
2 stores instructions that enable the system to resume cache
3 operations after shutting off the cache memory in response
4 to a cache condition by initially resuming reduced speed
5 operations in a first stage and thereafter resuming normal
6 operations.

1 34. The system of claim 26 wherein said cache memory
2 includes a temperature sensor.

1 35. A circuit comprising:
2 a component to receive an indication of the
3 temperature of a cache memory and to develop a signal to
4 transition the cache memory from a write-back cache to a
5 write-through cache in response to said temperature
6 indication.

1 36. The circuit of claim 35 wherein said component to
2 vary the operation of a system to adjust for the
3 temperature affected operation of said cache memory.

1 37. The circuit of claim 36 wherein said component to
2 adjust a caching operation of the system in response to a
3 temperature indication from said memory.

1 38. The circuit of claim 36 wherein said component to
2 shut off said cache in response to a temperature
3 indication.

1 39. The circuit of claim 38 wherein said component to
2 invalidate a cache line in said cache memory.

1 40. The circuit of claim 35 including a cache memory.

1 41. The circuit of claim 40 including a ferroelectric
2 polymer memory.

1 42. The circuit of claim 40 wherein said cache memory
2 includes a temperature sensor.

1 43. An integrated circuit comprising:
2 a ferroelectric polymer memory array; and
3 a temperature sensor.

1 44. The circuit of claim 43 wherein said array is a
2 cache memory.

1 45. The circuit of claim 44 wherein said array is a
2 disc cache memory.